

FORM PTO-1449 U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket Number:
5308-156

Serial No.:
09/911,995

LIST OF DOCUMENTS CITED BY APPLICANT

(Use several sheets if necessary)

Applicants: Ryu et al.

Filing Date: July 24, 2001

Group:
2811

U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
<i>GMH</i>	1	6,767,843	07/27/04	Lipkin et al.	438	758	
	2	6,759,684	07/06/04	Fukuda et al.	257	77	
	3	6,653,659	11/25/03	Ryu et al.	257	77	
	4	6,551,865	04/22/03	Kumar et al.	438	137	
	5	6,429,041	08/06/02	Ryu et al.	438	105	
	6	6,303,508	10/16/01	Alok	438	705	
	7	6,297,100	10/02/01	Kumar et al.	438	268	
	8	6,180,958	01/30/01	Cooper, Jr.	257	77	
	9	6,133,587	10/17/00	Takeuchi et al.	257	77	
	10	6,025,233	02/15/00	Teresawa	438	270	
	11	6,020,600	02/01/00	Miyajima et al.	257	76	
	12	5,976,936	11/02/99	Miyajima et al.	438	268	
	13	5,917,203	06/29/99	Bhatnagar et al.	257	139	
	14	5,877,041	03/02/99	Fuller	438	105	
	15	5,851,908	12/22/98	Harris et al.	438	520	
	16	5,837,572	11/17/98	Gardner et al.	438	199	
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	18	5,804,483	09/08/98	Harris	438	268	
	19	5,734,180	03/31/98	Malhi	257	77	
	20	5,710,059	01/20/98	Rottner	437	151	
	21	5,629,531	05/13/97	Palmour	257	77	
	22	5,510,281	04/23/96	Ghezze et al.	437	41	
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<i>GMH</i>	26	5,384,270	01/24/95	Ueno	437	40	

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29	5,111,253	05/05/92	Korman et al.	257	341		
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38	EP 1 204 145 A2	08/05/02	EPO				
39	EP 1 058 317 A2	12/06/00	EPO				
40	JP 01117363	05/10/89	Japan			Abstract	
41	JP 03034466	02/14/91	Japan			Abstract	
42	WO 97/98754	03/06/97	PCT				
43	WO 98/02916	01/22/98	PCT				
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45	Baliga, Power Semiconductor Devices, Chapter 7, PWS Publishing, 1996						
46	Bhatnagar et al. "Comparison of 6H-SiC, 3C-SiC, and Si for Power Devices," <i>IEEE Transactions on Electron Devices</i> , Vol. 40, No. 3, March 1993, pp. 645-55.						
47	Chung et al., "The Effect of Si:C Source Ratio on SiO ₂ /SiC Interface State Density for Nitrogen Doped 4H and 6H-SiC," <i>Materials Science Forum</i> . (2000) Vols. 338-342, pp. 1097-1100.						
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<i>29/7/01</i>	49	Mondal et al. "An Integrated 500-V Power DSMOSFET/Antiparallel Rectifier Device with Improved Diode Reverse Recovery Characteristics," <i>IEEE Electron Device Letters</i> , Vol. 23, No. 9, September 2002, pp. 562-4.	
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<i>29/7/01</i>	53	Rao et al. "Al and N Ion Implantations in 6H-SiC," <i>Silicon Carbide and Related Materials</i> . 1995 Conf, Kyoto, Japan. Published 1996.	
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